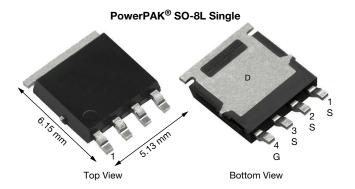
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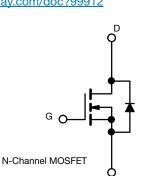
Automotive N-Channel 80 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY			
V _{DS} (V)	80		
$R_{DS(on)} (\Omega)$ at $V_{GS} = 10 V$	0.0095		
I _D (A)	57		
Configuration	Single		
Package	PowerPAK SO-8L		

FEATURES

- TrenchFET[®] power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishav.com/doc?99912</u>



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	Rc	ьН	S

COMPLIANT HALOGEN

ABSOLUTE MAXIMUM RATINGS ($T_C = 25 \text{ °C}$, unless otherwise noted)						
PARAMETER		SYMBOL	LIMIT	UNIT		
Drain-source voltage		V _{DS}	80	V		
Gate-source voltage		V _{GS}	± 20	v		
Continuous drain current	T _C = 25 °C T _C = 125 °C	- I _D -	57			
	T _C = 125 °C		33			
Continuous source current (diode conduction)		I _S	60	А		
Pulsed drain current ^a		I _{DM}	150			
Single pulse avalanche current	L = 0.1 mH	I _{AS}	33			
Single pulse avalanche energy	L = 0.1 IIIH	E _{AS}	54	mJ		
Maximum power dissipation ^a	T _C = 25 °C	Р	68	W		
	T _C = 125 °C	P _D	22			
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	°C		
Soldering recommendations (peak temperature) c, d			260			

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-ambient	PCB mount ^b	R _{thJA}	68	°C/W	
Junction-to-case (drain)	on-to-case (drain)		2.2	C/W	

Notes

b. When mounted on 1" square PCB (FR4 material).

d. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

a. Pulse test; pulse width $\leq 300~\mu\text{s},$ duty cycle $\leq 2~\%.$

c. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

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PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static					•		•	
Drain-source breakdown voltage	V _{DS}	$V_{GS}=0,\ I_D=250\ \mu A$		80	-	-	v	
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$		3.0	3.5	v	
Gate-source leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	-	± 100	nA	
Zero gate voltage drain current		$V_{GS} = 0 V$	V _{DS} = 80 V	-	-	1		
	I _{DSS}	$V_{GS} = 0 V$	$V_{DS} = 80 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$	-	-	50	μA	
		$V_{GS} = 0 V$	V _{DS} = 80 V, T _J = 175 °C	-	-	150		
On-state drain current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	30	-	-	Α	
		V _{GS} = 10 V	I _D = 10 A	-	0.0078	0.0095		
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 10 A, T _J = 125 °C	-	-	0.0152	Ω	
		V _{GS} = 10 V	I _D = 10 A, T _J = 175 °C	-	-	0.0188		
Forward transconductance ^b	g fs	V _{DS} = 15 V, I _D = 10 A		-	36	-	S	
Dynamic ^b					•			
Input capacitance	C _{iss}	V _{GS} = 0 V	V _{DS} = 25 V, f = 1 MHz	-	2005	2650	pF	
Output capacitance	Coss			-	1055	1400		
Reverse transfer capacitance	C _{rss}			-	36	50		
Total gate charge ^c	Qg			-	30	45		
Gate-source charge ^c	Q _{gs}	V _{GS} = 10 V	$_{\rm S} = 10 \text{ V}$ $V_{\rm DS} = 40 \text{ V}, \text{ I}_{\rm D} = 5 \text{ A}$	-	9	-	nC	
Gate-drain charge ^c	Q _{gd}			-	5	-		
Gate resistance	Rg	f = 1 MHz		0.20	0.45	0.68	Ω	
Turn-on delay time ^c	t _{d(on)}	$V_{DD}=40~V,~R_L=8~\Omega$ $I_D\cong 5~A,~V_{GEN}=10~V,~R_g=1~\Omega$		-	15	25		
Rise time ^c	t _r			-	5	10	ns	
Turn-off delay time ^c	t _{d(off)}			-	24	40		
Fall time ^c	t _f			-	14	25		
Source-Drain Diode Ratings and Charac	teristics ^b	<u> </u>				1		
Pulsed current ^a	I _{SM}			-	-	150	Α	
Forward voltage	V _{SD}	I _F = 10 A, V _{GS} = 0		-	0.8	1.2	V	
Body diode reverse recovery time	t _{rr}	I _F = 10 A, di/dt = 100 A/μs		-	57	115	ns	
Body diode reverse recovery charge	Q _{rr}			-	88	180	nC	
Reverse recovery fall time	t _a			-	27	-	ns	
Reverse recovery rise time	t _b			-	31	-	113	
Body diode peak reverse recovery current	I _{RM(REC)}			-	-2.9	-6	Α	

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

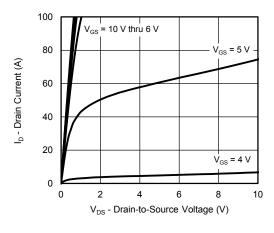
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

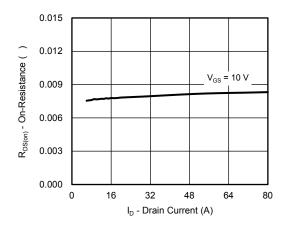


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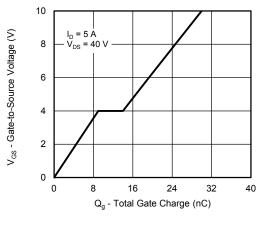
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



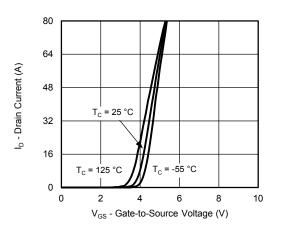
Output Characteristics



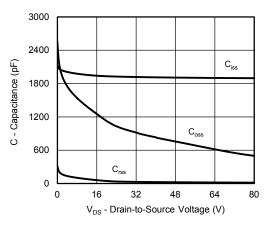
On-Resistance vs. Drain Current



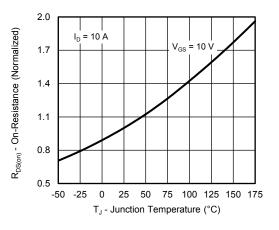
Gate Charge



Transfer Characteristics



Capacitance



On-Resistance vs. Junction Temperature

S16-2322-Rev. A, 14-Nov-16

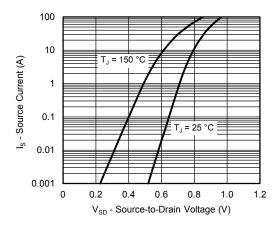
3 stions, contact: automostechsupp Document Number: 75095

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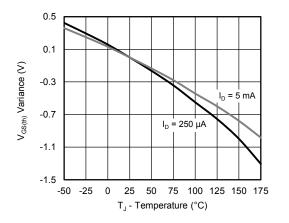


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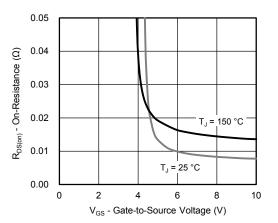
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



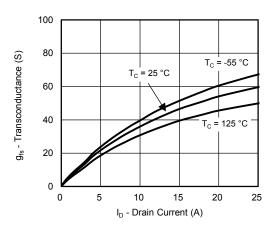
Source Drain Diode Forward Voltage



Threshold Voltage

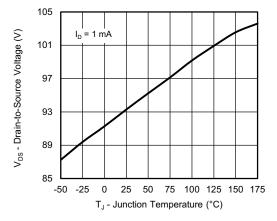


On-Resistance vs. Gate-to Source Voltage





Transconductance



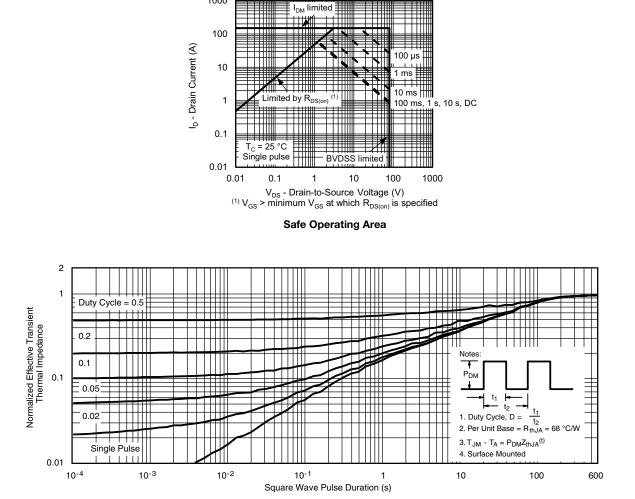
Drain Source Breakdown vs. Junction Temperature

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TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

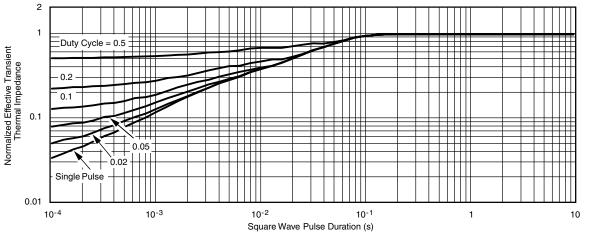


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TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

• The characteristics shown in the two graphs

S16-2322-Rev. A, 14-Nov-16

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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